

40V PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Complementary NPN Type Available (MMBT3904LP)
- Ultra-Small Leadless Surface Mount Package
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- ESD rating: 200V-MM, 4KV-HBM

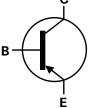
Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)

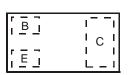
X1-DFN1006-3



Bottom View



Device Symbol



Top View Device Schematic

Ordering Information

Notes:

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT3906LP-7	3N	7	8mm	3,000
MMBT3906LP-7B	3N	7	8mm	10,000

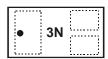
1. No purposefully added lead.

2. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com.

3. For packaging details, go to our website at http://www.diodes.com.

Marking Information

MMBT3906LP-7



Top View Dot Denotes Collector Side

MMBT3906LP-7B



Top View Bar Denotes Base and Emitter Side 3N = Product Type Marking Code



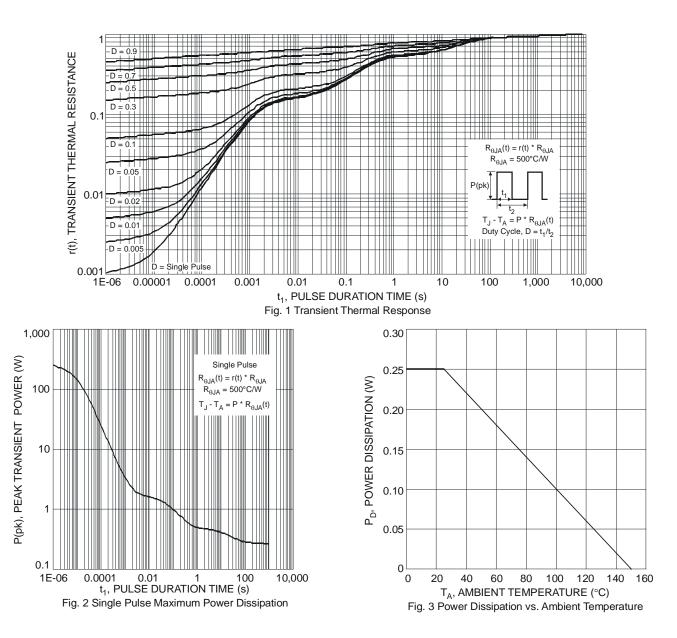
Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current - Continuous (Note 4)	Ι _C	-200	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	PD	250	mW
Thermal Resistance, Junction to Ambient (Note 4)	$R_{ heta JA}$	500	°C/W
Operating and Storage and Temperature Range	TJ, TSTG	-55 to +150	۵°

Notes: 4. Device mounted on FR-4 PCB, pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com

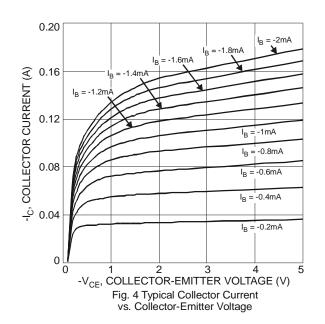


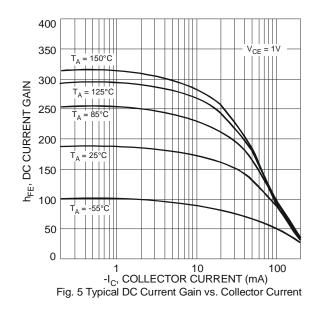


Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition	
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-40		V	$I_{\rm C} = -10\mu A, I_{\rm E} = 0$	
Collector-Emitter Breakdown Voltage (Note 5)	BVCEO	-40	_	V	$I_{\rm C} = -1.0 \text{mA}, I_{\rm B} = 0$	
Emitter-Base Breakdown Voltage	BV _{EBO}	-5.0	_	V	$I_{\rm E} = -10\mu A, I_{\rm C} = 0$	
-	I _{CEX}	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$	
Collector Cutoff Current	I _{CBO}	_	-50	nA	$V_{CB} = -30V, I_E = 0$	
Base Cutoff Current	I _{BL}	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$	
ON CHARACTERISTICS (Note 5)	52		•	1		
		60	_		$I_{C} = -100 \mu A$, $V_{CE} = -1.0 V$	
		80	_		I _C = -1.0mA, V _{CE} = -1.0V	
DC Current Gain	h _{FE}	100	300		I _C = -10mA, V _{CE} = -1.0V	
		60	_		$I_{C} = -50 \text{mA}, V_{CE} = -1.0 \text{V}$	
		30	_		$I_{C} = -100 \text{mA}, V_{CE} = -1.0 \text{V}$	
Collector-Emitter Saturation Voltage		—	-0.25	V	$I_{C} = -10mA$, $I_{B} = -1.0mA$	
Collector-Emilier Saturation voltage	V _{CE(sat)}	_	-0.40		$I_{C} = -50 \text{mA}, I_{B} = -5.0 \text{mA}$	
Base-Emitter Saturation Voltage	V	-0.65	-0.85	V	$I_{C} = -10mA$, $I_{B} = -1.0mA$	
Dase-Emilier Saturation Voltage	V _{BE(sat)}		-0.95		$I_{C} = -50 \text{mA}, I_{B} = -5.0 \text{mA}$	
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}		4.5	pF	$V_{CB} = -5.0V, f = 1.0MHz, I_E = 0$	
Input Capacitance	C _{ibo}		10	pF	$V_{EB} = -0.5V, f = 1.0MHz, I_{C} = 0$	
Input Impedance	h _{ie}	2.0	12	kΩ		
Voltage Feedback Ratio	h _{re}	0.1	10	x 10 ⁻⁴	$V_{CE} = 10V, I_C = 1.0mA,$	
Small Signal Current Gain	h _{fe}	100	400		f = 1.0kHz	
Output Admittance	h _{oe}	3.0	60	μS		
Current Gain-Bandwidth Product	f _T	300	—	MHz	$V_{CE} = -20V, I_C = -10mA,$ f = 100MHz	
SWITCHING CHARACTERISTICS						
Delay Time	t _d	—	35	ns	$V_{CC} = -3.0V, I_C = -10mA,$	
Rise Time	tr	_	35	ns	$V_{BE(off)} = 0.5V, I_{B1} = -1.0mA$	
Storage Time	ts		225	ns	$V_{CC} = -3.0V, I_C = -10mA,$	
Fall Time	t _f	_	75	ns	$I_{B1} = I_{B2} = -1.0 \text{mA}$	

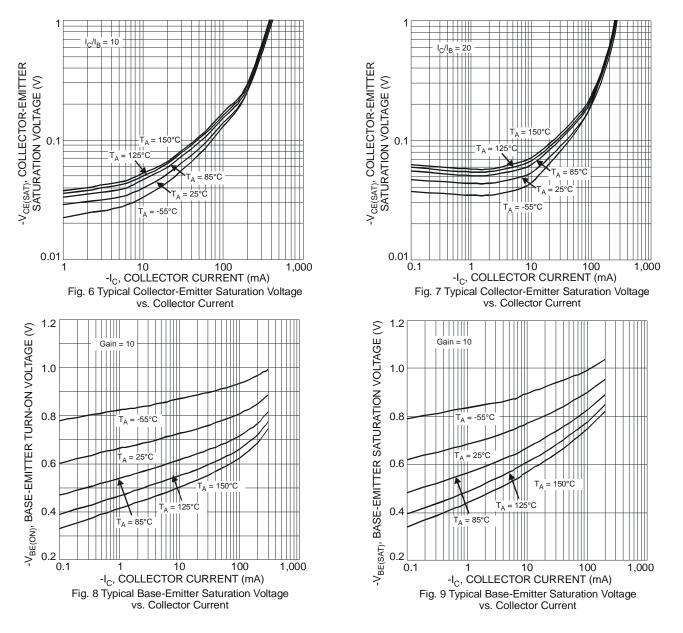
Notes: 5. Short duration pulse test used to minimize self-heating effect.



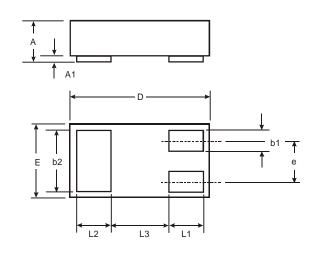




MMBT3906LP



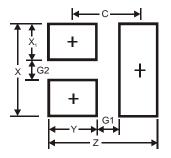
Package Outline Dimensions



X1-DFN1006-3				
Dim	Min	Max	Тур	
Α	0.47	0.53	0.50	
A1	0	0.05	0.03	
b1	0.10	0.20	0.15	
b2	0.45	0.55	0.50	
D	0.95	1.075	1.00	
Е	0.55	0.675	0.60	
e			0.35	
L1	0.20	0.30	0.25	
L2	0.20	0.30	0.25	
L3			0.40	
All Dimensions in mm				



Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
Х	0.7
X1	0.25
Y	0.4
С	0.7

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

- 1. are intended to implant into the body, or
- 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2011, Diodes Incorporated

www.diodes.com